 INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)	ATTY DOCKET NO. ITL 1063US (P18030)	SERIAL NO. 10/692,696
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Ch	K.	JP 63 013379	06/21/1988	Japan			Abstract Only	
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	Q.						
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EXAMINER 	DATE CONSIDERED 01-05-06
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.